

TDSEMIC

拓電半導體

自主封測 品質把控 售後保障

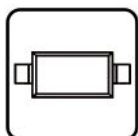
WEB | WWW.TDSEMIC.COM



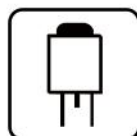
電源管理



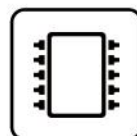
顯示驅動



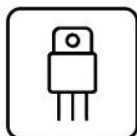
二三極管



LDO穩壓器



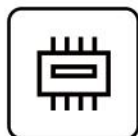
觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

BCP56-TD

產品規格說明書

BCP56-TD NPN Plastic-Encapsulate Transistors

Features

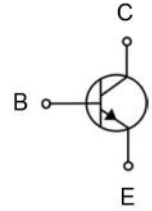
- Collector Current: $I_C=1A$
- Power Dissipation of 1.5W

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
BCP5x	SOT-223	BCP5x	1000

x:From 4/5/6

SOT-223



Maxmim Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	BCP54	45	V
	BCP55	60	
	BCP56	100	
Collector-Emitter Voltage	BCP54	45	V
	BCP55	60	
	BCP56	80	
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Collector Power Dissipation	P_C	1.5	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	83.3	°CW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Classification Of h_{FE}

Rank	BCP54-10, BCP55-10, BCP56-10	BCP54-16, BCP55-16, BCP56-16
Range	63-160	100-250
Marking	BCP54-10, BCP55-10, BCP56-10	BCP54-16, BCP55-16, BCP56-16

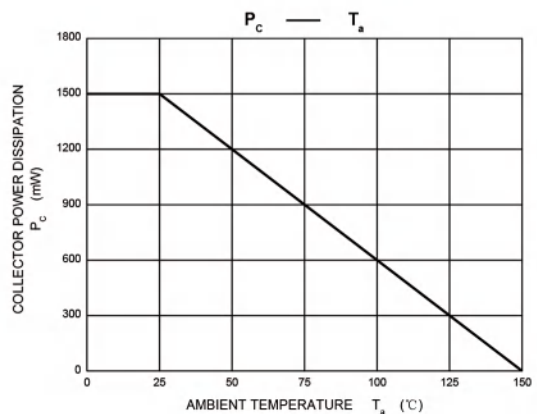
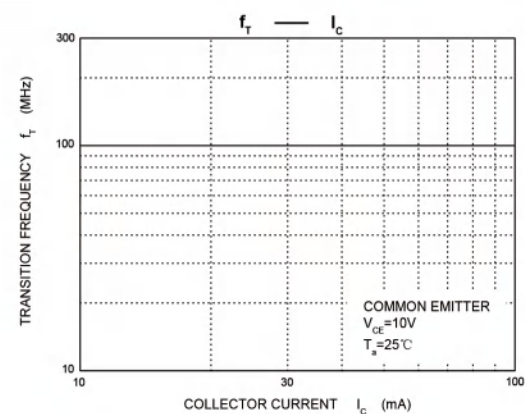
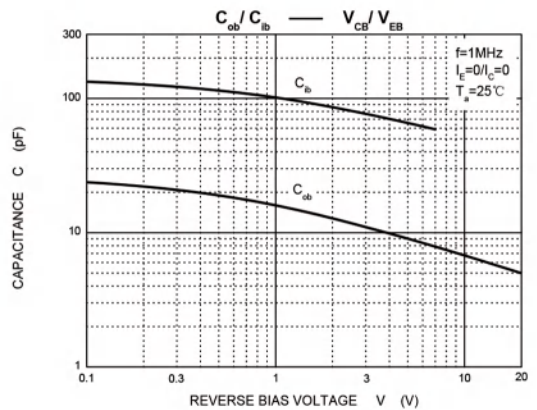
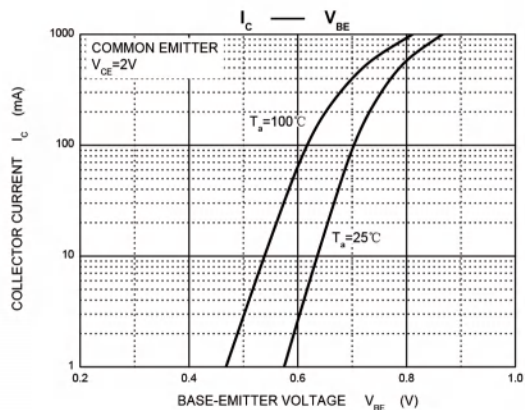
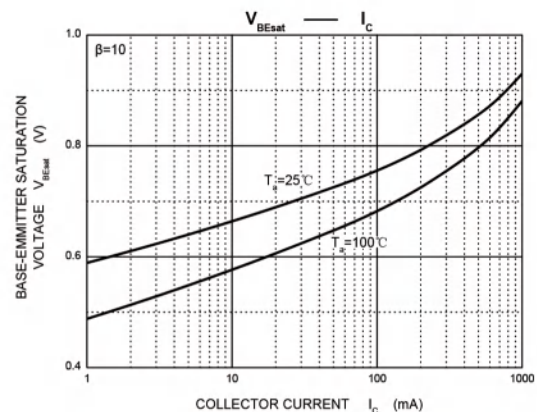
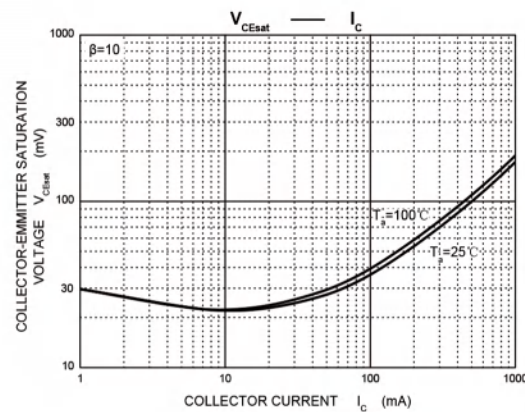
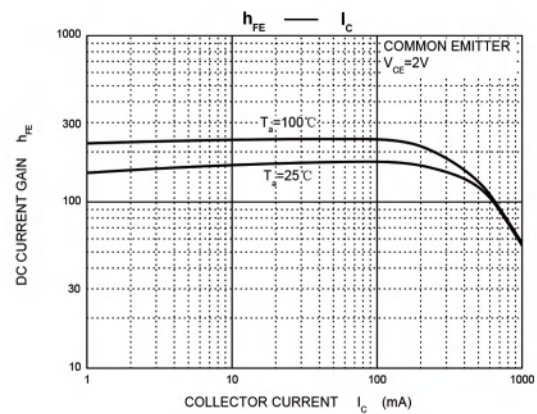
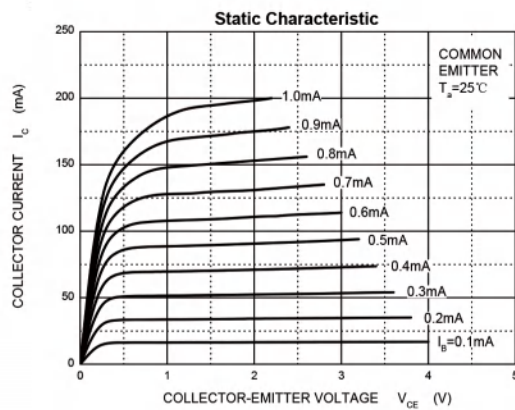
BCP56-TD NPN Plastic-Encapsulate Transistors

Electrical Characteristics (Ta=25°C unless otherwise specified)

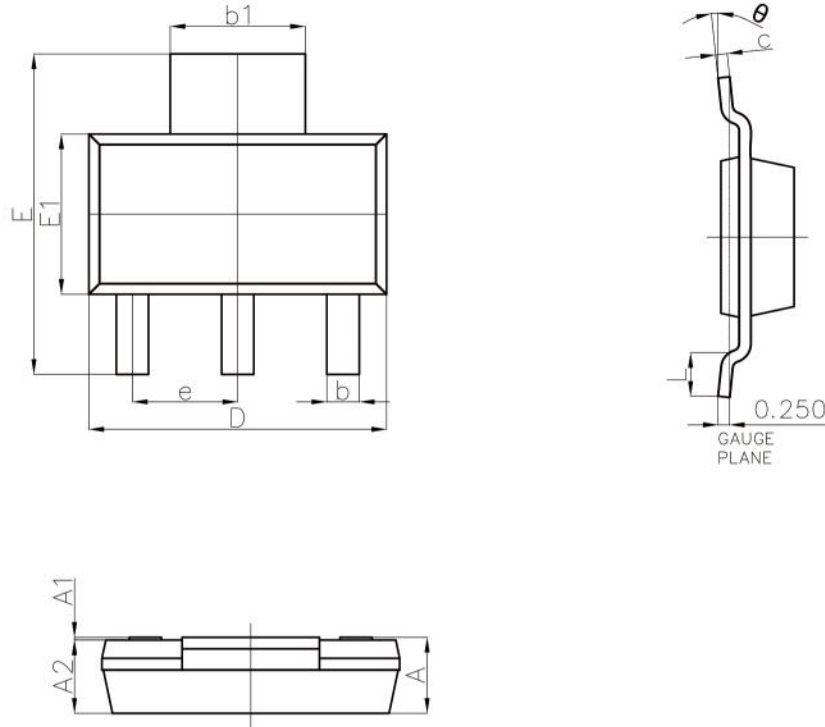
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	BCP54	$V_{(BR)CBO}$ $I_C = 0.1mA, I_E = 0$	45		V
	BCP55		60		
	BCP56		100		
Collector-emitter breakdown voltage	BCP54	$V_{(BR)CEO}$ $I_C = 10mA, I_B = 0$	45		V
	BCP55		60		
	BCP56		80		
Base-emitter breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 30V, I_E = 0$		100	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = 2V, I_C = 5mA$	25		
	$h_{FE(2)}$	$V_{CE} = 2V, I_C = 150mA$	63	250	
	$h_{FE(3)}$	$V_{CE} = 2V, I_C = 500mA$	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$		0.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = 2V, I_C = 500mA$		1	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 50mA, f = 100MHz$	100		MHz

BCP56-TD NPN Plastic-Encapsulate Transistors

Typical Characteristics



Package Dimensions SOT-223



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	—	1.800	—	0.071
A1	0.020	0.100	0.001	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.840	0.026	0.033
b_1	2.900	3.100	0.114	0.122
c	0.230	0.350	0.009	0.014
D	6.300	6.700	0.248	0.264
E	6.700	7.300	0.264	0.287
E_1	3.300	3.700	0.130	0.146
e	2.300(BSC)		0.091(BSC)	
L	0.750	—	0.030	—
θ	0°	10°	0°	10°